

Code: CE2T3, CS2T3, IT2T3

I B.Tech - II Semester – Regular Examinations – April 2016

ENGINEERING PHYSICS
(Common for CE, CSE & IT)

Duration: 3 hours

Max. Marks: 70

PART – A

Answer *all* the questions. All questions carry equal marks

11x 2 = 22 M

1. a) What are the conclusions of de- Broglies Hypothesis?
- b) What is Heisenberg uncertainty principal?
- c) Explain the significance of Miller indices.
- d) Define and explain the space lattice.
- e) Mention the important failures of Classical free electron Theory.
- f) Define Dielectric constant.
- g) Explain the concept of Feerimagnetism.
- h) Write about Fermi level in intrinsic the Semi conductor.
- i) Explain the Population inversion condition.
- j) Write the principle of an Optical Fibre.
- k) What are nanomaterials.

PART – B

Answer any **THREE** questions. All questions carry equal marks.

3 x 16 = 48 M

2. a) Describe the construction and working of Davison and Germer experiment to estimate the dual nature of Material particle. 12 M
- b) Calculate the de- Broglies wave length of an electron which has been accelerated from rest on application of potential of 400 volts. 4 M
3. a) Explain a short note on seven types of Crystal systems. 6 M
- b) Find the packing fraction of SC, BCC, and FCC crystals. 6 M
- c) A beam of X-rays is incident on a Nacl crystal with lattice spacing 0.282 nm. Calculate the wavelength of X- rays if the first order Bragg reflection takes place at a glancing angle of $8^{\circ} 35'$. 4 M
4. a) Derive the expression for the electronic polarisability of a dielectric material 10 M
- b) Derive the Classius-Mossotti relation. 4 M

- c) The dielectric constant of He gas at NTP is 1.0000684.
Calculate the electronic polarisability of He atoms if the
gas contains 2.7×10^{25} atoms/m³. 2 M
5. a) Distinguish between intrinsic and extrinsic semiconductor. 6 M
- b) Derive an expression for the carrier concentration of an n-type semiconductor. 6 M
- c) Discuss Fermi level in p type semiconductors. 4 M
6. a) Discuss the electrical and mechanical properties of nanomaterials. 6 M
- b) Explain the synthesis of nanomaterials by Sol-Gel method with a neat flow chart. 6 M
- c) Write any two applications of LASERS in defense. 4 M